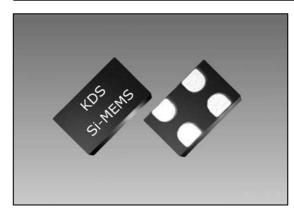
High Temperature MEMS Oscillator



MO8918



Features

- Frequencies between 1 MHz to 110 MHz accurate 6 decimal places
 Industry-Standard packages:
 - 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm
- Excellent total frequency stability as low as ±20 x 10⁻⁶
- Low power consumption of +3.5 mA typical at f = 20 MHz, Vdd = +1.8V
- Applications
- Industrial, medical, non AEC-Q100 automotive, avionics and other high temperature applications
- Industrial sensors, PLC, motor servo, outdoor networking equipment, medical video cam, asset tracking systems, etc



■Standard Specification

						Pts-frae Asi+5 Compilant
Item	Symbol	Min.	Тур.	Max.	Unit	Condition
Output Frequency Range	f	1	_	110	MHz	Refer to datasheet for exact list of supported frequencies
Supply Voltage	Vdd	+1.62	+1.8	+1.98	v	
		+2.25	+2.5	+2.75		
		+2.52	+2.8	+3.08		
		+2.7 +2.97	+3.0	+3.3		
		+2.97	+3.3	+3.63 +3.63		
Operating Temperature	_	-40	_	+105		Extended Industrial
Range (ambient)	T_use	-40	_	+125	°C	Automotive
Frequency Stability	F_stab	-20	-	+20	x10 ⁻⁶	Inclusive of Initial tolerance at +25°C, 1st year aging at +25°C,
		-25	-	+25		and variations over operating temperature, rated power supply
		-30	-	+30		voltage and load (15 pF \pm 10%).
		-50	-	+50		
Current Consumption	ldd	-	+3.8 +3.6	+4.7 +4.5	mA	No load condition, $f = 20 \text{ MHz}$, Vdd = +2.8V, +3.0V or +3.3V No load condition, $f = 20 \text{ MHz}$, Vdd = +2.5V
			+3.6	+4.5		No load condition, $f = 20$ MHz, $Vdd = +2.5V$ No load condition, $f = 20$ MHz, $Vdd = +1.8V$
		-	+3.5	+4.5		Vdd = $+2.5V$ to $+3.3V$, OE = Low, Output in high Z state
OE Disable Current	I_od	_		+4.3	mA	Vdd = +1.8V, OE = Low, Output in high Z state
Standby Current			+2.6	+8.5		· -
	I_std	-	-		μA	Vdd = +2.8V to +3.3V, \overline{ST} = Low, Output is weakly pulled down
		-	+1.4	+5.5		Vdd = +2.5V, ST = Low, Output is weakly pulled down
		-	+0.6	+4.0		Vdd = +1.8V, ST = Low, Output is weakly pulled down
Duty Cycle	DC	45	-	55	%	All Vdds
Output Low Voltage	V _{OL}					I _{oL} = +4.0 mA (Vdd = +3.0V or +3.3V)
			Vdd x 0.1	V	I _{OL} = +3.0 mA (Vdd = +2.8V or +2.5V)	
						I _{oL} = +2.0 mA (Vdd = +1.8V)
Output High Voltage	V _{OH}			_		I _{OH} = -4.0 mA (Vdd = +3.0V or +3.3V)
		Vdd x 0.9 –	_			$I_{OH} = -3.0 \text{ mA} (Vdd = +2.8 \text{ V or } +2.5 \text{ V})$
				-	$I_{OH} = -2.0 \text{ mA} (Vdd = +1.8V)$	
		_	1.0	2.0		Vdd = +2.5V, +2.8V, +3.0V or +3.3V, 20% - 80%
Rise/Fall Time	Tr,Tf		1.3	2.0	ns	Vdd = +1.8V, 20% - 80%
		_	1.0	3.0		Vdd = +2.25V - +3.63V, 20% - 80%
Input Low Voltage	V _{IL}	_	_	Vdd x 0.3	V	Pin 1, OE or ST
Input High Voltage	V _{IH}	Vdd x 0.7	_	_	V	Pin 1, OE or ST
Startup Time	T_start	_	_	5.0	ms	Measured from the time Vdd reaches its rated minimum value
Enable/Disable Time	T_oe	-	_	130	ns	f = 110 MHz. For other frequencies, T_oe = 100 ns + 3 * cycles
Resume Time	T_resume	_	_	5.0	ms	Measured from the time \overline{ST} pin crosses 50% threshold
RMS Period Jitter	T_jitt	-	1.6	2.5	ps	f = 75 MHz, Vdd = +2.5V, +2.8V, +3.0V or +3.3V
		-	1.9	3.0		f = 75 MHz, Vdd = +1.8V
Peak-topeak Period Jitter	T_pk	_	12	20	ps	f = 75 MHz, Vdd = +2.5V, +2.8V, +3.0V or +3.3V
		_	<u>14</u> 0.5	25		f = 75 MHz, Vdd = +1.8V f = 75 MHz, Integration bandwidth = 900 kHz to 7.5 MHz
RMS Phase Jitter (random)	T_phj		1.3	0.8	ps	f = 75 MHz, integration bandwidth = 900 KHz to 7.5 MHz f = 75 MHz, integration bandwidth = 12 kHz to 20 MHz
		_	1.0	2.0	<u> </u>	$\mu = r_0 \text{ winz}, \text{ megration ballowidth} = r_2 \text{ KHZ to zo winz}$

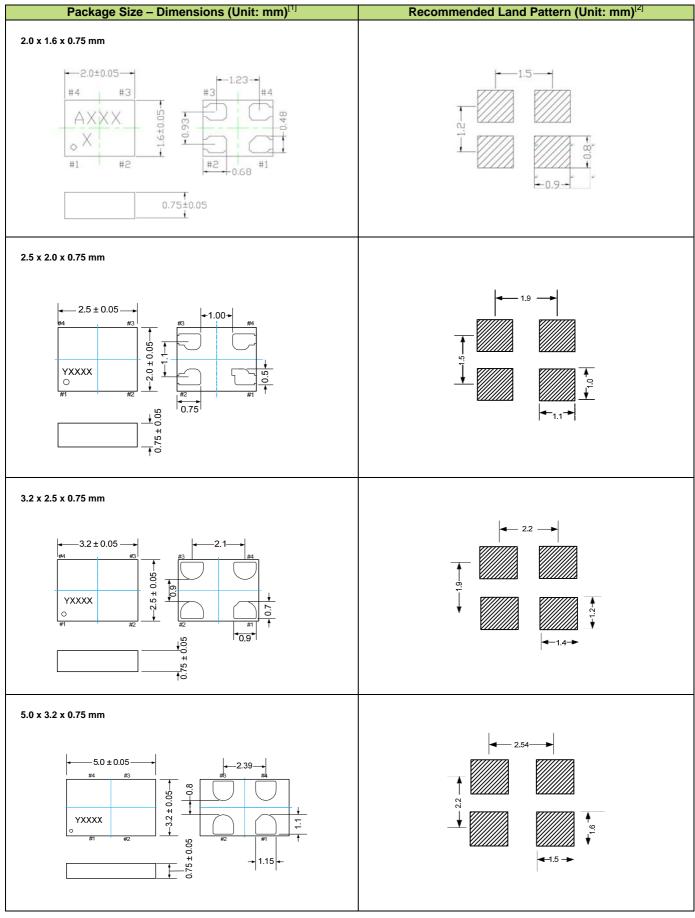
Consult our sales representative for other specifications.

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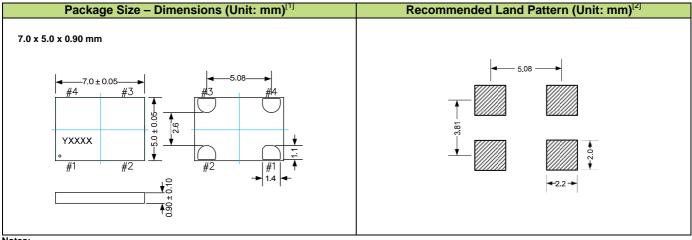
Dimensions and Patterns





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Dimensions and Patterns



Notes:

Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
 A capacitor of value 0.1 μF between Vdd and GND is required.